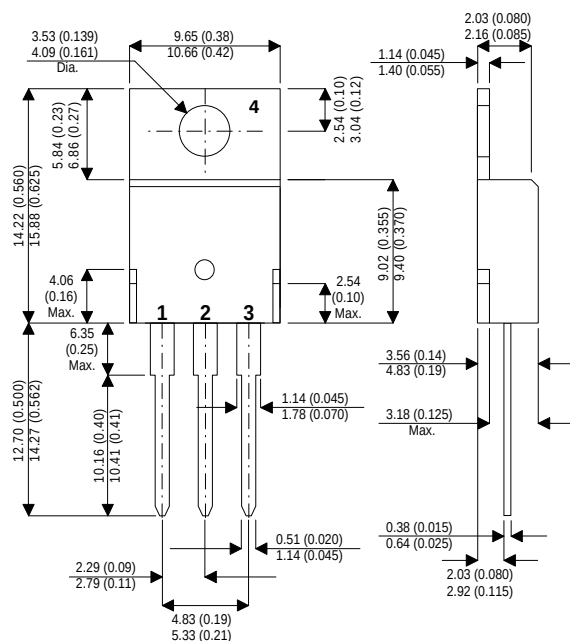


MECHANICAL DATA

Dimensions in mm



TO-220AB

Pin 1 – Base Pin 2 – Collector Pin 3 – Emitter
Back Metal is Collector.

COMPLEMENTARY SILICON POWER TRANSISTORS

For use as high frequency
drivers in audio amplifiers.

ABSOLUTE MAXIMUM RATINGS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

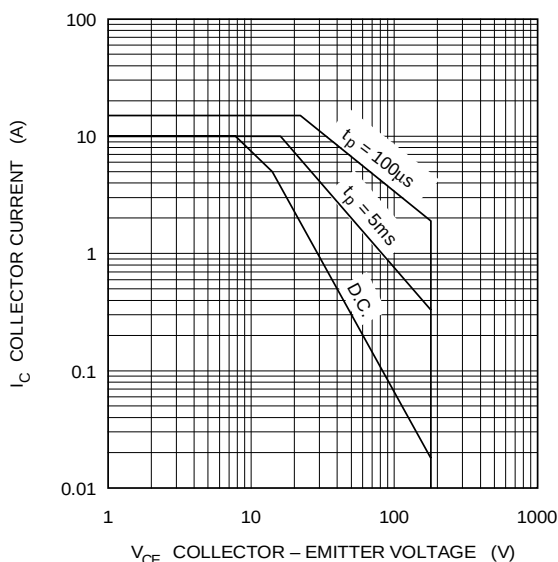
V_{CBO}	Collector – Base Voltage	240V
V_{CEO}	Collector – Emitter Voltage ($I_{\text{B}} = 0$)	160V
V_{EBO}	Emitter – Base Voltage	5V
I_{C}	Collector Current	8A
$I_{\text{C(PK)}}$	Peak Collector Current	16A
I_{B}	Base Current	2A
P_{D}	Total Dissipation at $T_{\text{C}} = 25^{\circ}\text{C}$	60W
	Derate above 25°C	0.48°C/W
P_{D}	Total Dissipation at $T_{\text{A}} = 25^{\circ}\text{C}$	2W
	Derate above 25°C	0.016°C/W
T_{stg}	Operating and Storage Temperature Range	-65 to 150°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

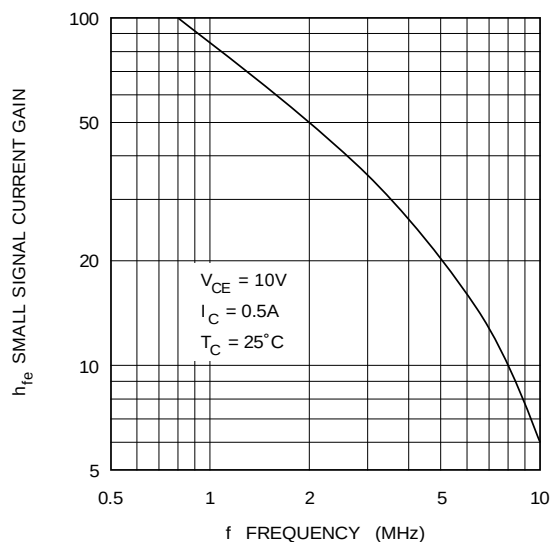
Parameter		Test Conditions		Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS							
V _{CEO(sus)} *	Collector – Emitter Sustaining Voltage	I _C = 10mA	I _B = 0	160			V
I _{CEO}	Collector – Emitter Cut-Off Current	V _{CE} = 160V	I _B = 0			0.1	mA
I _{CBO}	Collector – Base Cut-Off Current	V _{CE} = 240V	I _E = 0			10	μA
I _{EBO}	Emitter Cut-Off Current	V _{BE} = 5V	I _C = 0			10	
ON CHARACTERISTICS							
h _{FE} *	DC Current Gain	I _C = 100mA	V _{CE} = 2V	40			—
		I _C = 2A	V _{CE} = 2V	40			
		I _C = 3A	V _{CE} = 2V	40			
		I _C = 4A	V _{CE} = 2V	20			
Linearity*	h _{FE} vs h _{FE} Ratio	h _{FE} @ I _C = 1 to 3A			2:1		—
V _{CE(sat)} *	Collector – Emitter Saturation Voltage	I _C = 1A	I _B = 100mA			0.4	V
		I _C = 3A	I _B = 300mA			0.5	
V _{BE(on)} *	Base – Emitter On Voltage	I _C = 1A	V _{CE} = 2V			1.0	V
		I _C = 3A	V _{CE} = 2V			1.0	
DYNAMIC CHARACTERISTICS							
f _T	Current Gain – Bandwidth Product f _T = h _{fe} • F _{test}	I _C = 500mA	V _{CE} = 10V	30			MHz
f _{test} = 10MHz							
THERMAL CHARACTERISTICS							
R _{θJC}	Thermal Resistance Junction – Case					2.5	°C/W
R _{θJA}	Thermal Resistance Junction – Ambient					62.5	

* Pulse test t_p = 300μs, δ ≤ 2%.

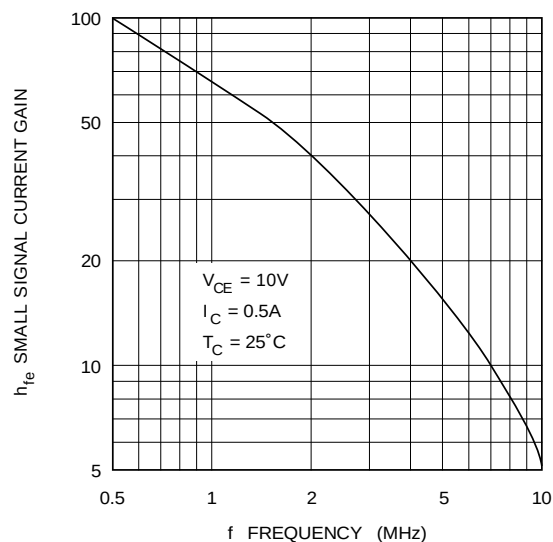
FORWARD BIAS SAFE OPERATING AREA



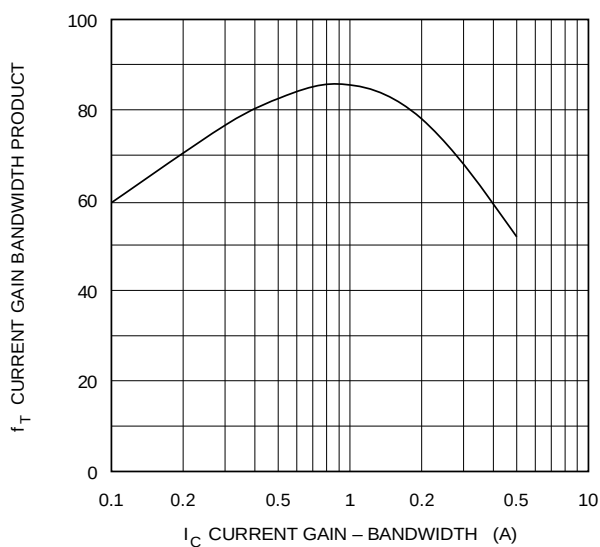
SMALL SIGNAL CURRENT GAIN – SM3177A



SMALL SIGNAL CURRENT GAIN – SM3178A



CURRENT GAIN BANDWIDTH PRODUCT SM3177A



CURRENT GAIN BANDWIDTH PRODUCT SM3178A

